Exhibit R-2, RDT&E Budget Item Justification: PB 2015 Defense Advanced Research Projects Agency

R-1 Program Element (Number/Name)

0400: Research, Development, Test & Evaluation, Defense-Wide I BA 3:

PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES

Date: March 2014

Advanced Technology Development (ATD)

Appropriation/Budget Activity

COST (\$ in Millions)	Prior Years	FY 2013	FY 2014	FY 2015 Base	FY 2015 OCO [#]	FY 2015 Total	FY 2016	FY 2017	FY 2018	FY 2019	Cost To Complete	Total Cost
Total Program Element	-	92.291	107.080	92.246	-	92.246	83.198	97.496	107.594	114.417	-	-
MT-12: MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY	-	36.797	32.336	12.386	-	12.386	-	-	-	-	-	-
MT-15: MIXED TECHNOLOGY INTEGRATION	-	55.494	74.744	79.860	-	79.860	83.198	97.496	107.594	114.417	-	-

[#] The FY 2015 OCO Request will be submitted at a later date.

A. Mission Description and Budget Item Justification

The Advanced Electronics Technologies program element is budgeted in the Advanced Technology Development Budget Activity because it seeks to design and demonstrate state-of-the-art manufacturing and processing technologies for the production of various electronics and microelectronic devices, sensor systems, actuators and gear drives that have military applications and potential commercial utility. Introduction of advanced product design capability and flexible, scalable manufacturing techniques will enable the commercial sector to rapidly and cost-effectively satisfy military requirements.

The MicroElectroMechanical Systems (MEMS) and Integrated Microsystems Technology project is a broad, cross-disciplinary initiative to merge computation and power generation with sensing and actuation to realize a new technology for both perceiving and controlling weapons systems and battlefield environments. MEMS applies the advantages of miniaturization, multiple components and integrated microelectronics to the design and construction of integrated electromechanical and electro-chemical-mechanical systems to address issues ranging from the scaling of devices and physical forces to new organization and control strategies for distributed, high-density arrays of sensor and actuator elements. The project will also address thermal management, navigation and positioning technology challenges.

The goal of the Mixed Technology Integration project is to leverage advanced microelectronics manufacturing infrastructure and DARPA component technologies developed in other projects to produce mixed-technology microsystems. These 'wristwatch size', low-cost, lightweight and low power microsystems will improve the battlefield awareness and security of the warfighter and the operational performance of military platforms. The chip assembly and packaging processes currently in use produce a high cost, high power, large volume and lower performance system. This program is focused on the monolithic integration of mixed technologies to form batch-fabricated, mixed technology microsystems 'on-a-single-chip' or an integrated and interconnected 'stack-of-chips'. The ability to integrate mixed technologies onto a single substrate will increase performance and reliability, while driving down size, weight, volume and cost.

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R-1 Program Element (Number/Name)

Appropriation/Budget Activity

0400: Research, Development, Test & Evaluation, Defense-Wide I BA 3:

PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES

Date: March 2014

Advanced Technology Development (ATD)

B. Program Change Summary (\$ in Millions)	FY 2013	FY 2014	FY 2015 Base	FY 2015 OCO	FY 2015 Total
Previous President's Budget	111.008	117.080	159.229	-	159.229
Current President's Budget	92.291	107.080	92.246	-	92.246
Total Adjustments	-18.717	-10.000	-66.983	-	-66.983
 Congressional General Reductions 	-0.147	-			
 Congressional Directed Reductions 	-7.477	-10.000			
 Congressional Rescissions 	-	-			
 Congressional Adds 	-	-			
 Congressional Directed Transfers 	-	-			
 Reprogrammings 	-8.181	-			
SBIR/STTR Transfer	-2.912	-			
 TotalOtherAdjustments 	-	-	-66.983	-	-66.983

Change Summary Explanation

FY 2013: Decrease reflects Congressional reductions for Sections 3001 & 3004, sequestration adjustments, reprogrammings, and the SBIR/STTR transfer.

FY 2014: Decrease reflects a reduction for prior year carryover.

FY 2015: Decrease reflects programs in thermal imaging coming to an end, micro position, navigation and timing scaling back and elimination of maskless nanowriter follow-on.

Exhibit R-2A, RDT&E Project J	ustification	: PB 2015 C	efense Adv	anced Res	earch Proje	cts Agency				Date: Mar	ch 2014		
Appropriation/Budget Activity 0400 / 3					PE 060373	am Elemen 39E I ADVAI NICS TECH	NCED	•	MT-12 / M	Number/Name) MEMS AND INTEGRATED SYSTEMS TECHNOLOGY			
COST (\$ in Millions)	Prior Years	FY 2013	FY 2014	FY 2015 Base	FY 2015 OCO #	FY 2015 Total	FY 2016	FY 2017	FY 2018	FY 2019	Cost To Complete	Total Cost	
MT-12: MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY	-	36.797	32.336	12.386	-	12.386	-	-	-	-	-	-	

[#] The FY 2015 OCO Request will be submitted at a later date.

A. Mission Description and Budget Item Justification

The MicroElectroMechanical Systems (MEMS) and Integrated Microsystems Technology program is a broad, cross-disciplinary initiative to merge computation and power generation with sensing and actuation to realize a new technology for both perceiving and controlling weapons systems and battlefield environments. Using fabrication processes and materials similar to those used to make microelectronic devices, MEMS applies the advantages of miniaturization, multiple components and integrated microelectronics to the design and construction of integrated electromechanical and electro-chemical-mechanical systems. The MEMS program addresses issues ranging from the scaling of devices and physical forces to new organization and control strategies for distributed, high-density arrays of sensor and actuator elements. These issues include microscale power and actuation systems as well as microscale components that survive harsh environments. Thermal management technologies will develop heat resistant thermal layers to provide efficient operation for cooling electronic devices. The current focus in micro technologies is to improve navigation, position and timing capabilities for uncompromised navigation and positioning in today's dynamic military field of operations.

B. Accomplishments/Planned Programs (\$ in Millions)	FY 2013	FY 2014	FY 2015	
Title: Micro-Technology for Positioning, Navigation, and Timing (Micro PN&T)	35.492	27.725	12.386	
Description: The Micro-Technology for Positioning, Navigation, and Timing (Micro-PN&T) program is developing low size, weight, power, and cost (SWaP+C) inertial sensors and timing sources. This suite of sensors, when integrated into an inertial measurement unit (IMU), will enable self-contained navigation and timing in the absence of signals from the Global Positioning System (GPS), due to environmental interference or adversary action such as GPS jamming. The Micro-PNT program is developing miniature high performance gyroscopes, accelerometers, and clocks, based on both solid state and atomic technologies. Advanced micro-fabrication techniques under development will enable the fabrication of a single package containing all the necessary devices in a volume the size of a sugar cube. The small SWaP+C of these technologies will enable ubiquitous guidance and navigation on all platforms, including guided munitions, unmanned aerial vehicles (UAVs), and individual soldiers.				
The successful realization of Micro-PN&T requires the development of new microfabrication processes and novel material systems for fundamentally different sensing modalities, understanding of the error sources at the micro-scale, and development of micro-scale systems for sensors based on atomic physics techniques. Innovative 3-D microfabrication techniques under development will allow co-fabrication of dissimilar devices on a single chip, such that clocks, gyroscopes, accelerometers, and				

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Exhibit R-2A, RDT&E Project Justification: PB 2015 Defense Ad	Ivanced Research Projects Agency	Date: N	March 2014	
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	Project (Number/ MT-12 / MEMS AN MICROSYSTEMS	ID INTEGRA	
B. Accomplishments/Planned Programs (\$ in Millions)		FY 2013	FY 2014	FY 2015
calibration stages can be integrated into a small, low power archite based on laser-cooled neutral atoms and trapped ions as well as in magnetic resonance. Applied research for this program is funded w	nertial sensors based on atomic interferometry and nuclea			
FY 2013 Accomplishments: - Developed monolithic microfabrication process to co-integrate clo - Demonstrated functionality of a co-fabricated 10 mm^3 IMU.				
 Developed an automated test station to provide extended testing Developed 3D micro shell resonators with integrated electrodes f Modeled the internal and external sources of error, scale-factor, a calibration. 	or drive and sense.			
 Demonstrated small ion clocks with fractional frequency stability Demonstrated NMR gyro operation up to 2,500deg/s rotation with Demonstrated efficacy of zero velocity updating and ultrasonic range achieving accuracy of position tracking to 4m after 2 hours of navig 	n turn-key operation. Inging for calibration of an IMU in dismount applications,			
FY 2014 Plans: - Demonstrate and evaluate performance of miniature atomic physical shell resonators, with quality factor (example to Evaluate performance of a complete 6-degree of freedom IMU with Demonstrate gyroscope self-calibration with long-term scale factors.	Q) over 1 Million, for gyroscope applications. ith a volume of < 10 mm^3.			
 FY 2015 Plans: Demonstrate hybrid IMU, including integration of atomic physics startup time less than one minute. Demonstrate gyroscope self-calibration with long-term scale factors. Demonstrate portable high-performance atomic frequency standards. 	or and bias of <1 ppm of full range.	with		
Title: Blast Exposure Accelerated Sensor Transfer (BEAST)		1.305	4.611	-
Description: The Blast Exposure Accelerated Sensor Transfer (BE program. Blast-related injuries have emerged as the signature wou exposure received by warfighters, which is critical for developing ar record such critical signatures as blast overpressure had to be deve to better understand the combat exposures responsible for these in The gauges have been effective at capturing such events during or	unds of recent conflicts. To better understand the level of nd providing better treatment, low-cost personal sensors to eloped. DARPA rapidly developed and fielded the Blast C njuries by properly capturing relevant data at the time of in	o Gauge jury.		

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Exhibit R-2A, RDT&E Project Justification: PB 2015 Defense Ad	lvanced Research Projects Agency		Date: M	larch 2014	
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	MT-12	Project (Number/Name) MT-12 / MEMS AND INTEGRAT MICROSYSTEMS TECHNOLOG		
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2013	FY 2014	FY 2015
from the first recording during an IED attack to the first use of sense Traumatic Brain Injury (TBI). Unexpectedly, gauge recordings have in noncombat situations. Typically these happen during training us military services require additional tools to begin properly using the (BEAST) program is a 1-year effort to provide additional tools for us	e shown that potentially hazardous exposures may also or ing weapon systems. As the Blast Gauge is being deplot device. The Blast Exposure Accelerated Sensor Transf	yed, er			
FY 2013 Accomplishments: Outfitted all task force members of the Combined-Joint-Special-Conducted laboratory evaluation and end-user-assessments den Provided Blast Gauge technical support to Marines in Afghanista Discovered that training exercises present a risk of blast exposur Measured and provided data on training exposures to all U.S. mil Established mathematical and operational techniques to provide measurements and operational data. Supported independent evaluations of Blast Gauge technology be effectively and offer a dependable platform for identifying injury.	nonstrating that the Blast Gauges work as designed. n. e. litary services. a detailed recreation of blast events from sensor	ork			
 FY 2014 Plans: Support medical studies using Blast Gauges as part of studies in: Provide end user training and support in the battlespace and COI Complete a database to store and organize Blast Gauge recording front-end to the database. Develop tools to analyze and visualize data uploaded to the data Validate and refine the re-creation process. Controlled blast testing Expand the event reconstruction capability. 	NUS. ngs, sustainment, and transition and develop a web-base base.				
, ,	Accomplishments/Planned Programs Su	btotals	36.797	32.336	12.3

C. Other Program Funding Summary (\$ in Millions)

N/A

Remarks

D. Acquisition Strategy

N/A

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E. Performance Metrics		
Specific programmatic performance metrics are listed above in the program a	ccomplishments and plans section.	

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Appropriation/Budget Activity 0400 / 3					PE 060373	39E <i>I ADVA</i>	t (Number/ NCED HNOLOGIES	,	• `	umber/Nan IXED TECH TION		
COST (\$ in Millions)	Prior Years	FY 2013	FY 2014	FY 2015 Base	FY 2015 OCO [#]	FY 2015 Total	FY 2016	FY 2017	FY 2018	FY 2019	Cost To Complete	Total Cost
MT-15: MIXED TECHNOLOGY INTEGRATION	-	55.494	74.744	79.860	-	79.860	83.198	97.496	107.594	114.417	-	-

[#] The FY 2015 OCO Request will be submitted at a later date.

A. Mission Description and Budget Item Justification

The goal of the Mixed Technology Integration project is to leverage advanced microelectronics manufacturing infrastructure and DARPA component technologies developed in other projects to produce mixed-technology microsystems. These 'wristwatch size', low-cost, lightweight and low power microsystems will improve the battlefield awareness, security of the warfighter and the operational performance of military platforms. At the present time, systems are fabricated by assembling a number of mixed-technology components: microelectromechanical systems (MEMS), microphotonics, microfluidics and millimeterwave/microwave. Each technology usually requires a different level of integration, occupies a separate silicon chip and requires off-chip wiring, and requires fastening and packaging to form a module. The chip assembly and packaging processes produce a high cost, high power, large volume and lower performance system. This program is focused on the monolithic integration of mixed technologies to form batch-fabricated, mixed technology microsystems 'on-a-single-chip' or an integrated and interconnected 'stack-of-chips'.

The field of microelectronics incorporates micrometer/nanometer scale integration and is the most highly integrated, low-cost and high-impact technology to date. Microelectronics technology has produced the microcomputer-chip that enabled or supported the revolutions in computers, networking and communication. This program extends the microelectronics paradigm to include the integration of heterogeneous or mixed technologies. This new paradigm will create a new class of 'matchbook-size', highly integrated device and microsystem architectures. Examples of component-microsystems include low-power, small-volume, lightweight, microsensors, microrobots and microcommunication systems that will improve and expand the performance of the warfighter, military platforms, munitions and Unmanned Air Vehicles (UAVs).

The program includes the integration of mixed materials on generic substrates including glass, polymers and silicon. The program is design and process intensive, using 'standard' processes and developing new semiconductor-like processes and technologies that support the integration of mixed-technologies at the micrometer/nanometer scale. The program includes the development of micrometer/nanometer scale isolation, contacts, interconnects and 'multiple-chip-scale' packaging for electronic, mechanical, fluidic, photonic and rf/mmwave/microwave technologies. For example, a mixed-technology microsystem using integrated microfluidics, MEMS, microphotonics, microelectronics and microwave components could provide a highly integrated, portable analytical instrument to monitor the battlefield environment, the physical condition of a warfighter, the identity of warfighters (friend or foe) or the combat readiness of equipment. The ability to integrate mixed technologies onto a single substrate will drive down the size, weight, volume, and cost of weapon systems while increasing their performance and reliability.

B. Accomplishments/Planned Programs (\$ in Millions)	FY 2013	FY 2014	FY 2015
Title: Endurance	14.588	22.800	36.747
Description: The Endurance program will develop technology for pod-mounted lasers to protect a variety of airborne platforms from emerging and legacy electro-optical IR guided surface-to-air missiles. The focus of the Endurance effort will be to develop			

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Establish OA DDTOE Design Lead for the DD 0045 Defense A	UNCLASSIFIED		Detech	In 004.4	
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Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	MT-1	ct (Number/N 5 / MIXED TE GRATION		,
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2013	FY 2014	FY 2015
and test ancillary subsystems, such as a command subsystem, a t framework, subsystem interfaces, and the design, integration, and This program is an early application of technology developed in the research for this program is budgeted in PE 0602702E, project TT-	testing of a form/fit/function brass-board laser counterme Excalibur program and will transition via industry. Applie				
FY 2013 Accomplishments: - Completed risk analysis of subsystems and their integration: Ide - Produced System Requirements Documents (SRDs) and Interface					
 FY 2014 Plans: Acquire threat devices and/or surrogates in preparation for live fi Complete the critical design of ancillary subsystems (power support framework). Complete the preliminary design for subsystem integration includes 	oly, thermal management, processing and control, mecha				
 FY 2015 Plans: Complete the critical design for subsystem integration. Integrate, assemble and bench-test the brassboard system. Test the brassboard laser weapon system at an outdoor test range. 	ge against a representative set of dynamic-threat targets.				
Title: Diverse & Accessible Heterogeneous Integration (DAHI)			-	17.944	20.30
Description: Prior DARPA efforts have demonstrated the ability to achieve near-ideal "mix-and-match" capability for DoD circuit design Semiconductor Materials On Silicon (COSMOS) program, in which with silicon complementary metal-oxide semiconductor (CMOS) circuits speed and very high circuit complexity/density, respectively). The will take this capability to the next level, ultimately offering the sear (for example, Gallium Nitride (GaN), Indium Phosphide, Gallium Armicroelectromechanical (MEMS) sensors and actuators, photonic estructures. This capability will revolutionize our ability to build true volume reductions for a wide array of system applications.	gners. Specifically, one such program was the Compound transistors of Indium Phosphide (InP) could be freely mix rouits to obtain the benefits of both technologies (very high Diverse & Accessible Heterogeneous Integration (DAHI) mless co-integration of a variety of semiconductor devices resenide, Antimonide Based Compound Semiconductors), devices (e.g., lasers, photo-detectors) and thermal management.	d ked h effort s			
This program has basic research efforts funded in PE 0601101E, 0602716E, Project ELT-01 The Advanced Technology Developme efforts to focus on the establishment of an accessible, manufacture	ent part of this program will leverage these complementar				

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Exhibit R-2A, RDT&E Project Justification: PB 2015 Defense	Advanced Research Projects Agency		Date: N	larch 2014	
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B. Accomplishments/Planned Programs (\$ in Millions)			FY 2013	FY 2014	FY 2015
a wide array of materials and devices (including, for example, menabled (e.g. CMOS) architectures on a common silicon substrated accessible foundry processes of DAHI technology and demonst and designs that leverage heterogeneous integration. By the emature, sustainable DAHI foundry service to be made available of DoD laboratory, Federally Funded Research and Developme FY 2014 Plans: - Develop a high-yield, high-reliability accessible manufacturing foundry activity providing heterogeneously integrated circuits wir Phosphide (InP) Heterojunction Bipolar Transistor (HBTs), Gallichigh-Q passive devices). - Establish heterogeneous integration design/simulation tool flomicrosystems integration. - Demonstrate capability for supporting multi-project wafer runs. - Accelerate development of circuit design techniques and methoricuit architectures.	ate platform. This part of the program is expected to culminal trations of advanced microsystems with innovative architectured of the program, this effort seeks to establish a technologic (with appropriate computer-aided design support) to a wide and Center (FFRDC), academic and industrial designers. The process flow which will be transitioned to a self-sustaining of the four materials/device technologies (Silicon (Si) CMOS, Income Nitride (GaN) High-electron-mobility transistor (HEMTs), how snecessary to realize the full potential of heterogeneous is using the heterogeneous foundry service under developme	ate in lires cally variety dium and			
FY 2015 Plans: - Continue to develop a high-yield, high-reliability accessible masustaining foundry activity providing heterogeneously integrated HBTs, GaN HEMTs, and high-Q passive devices). - Continue to demonstrate capability for supporting multi-project development.	d circuits with four materials/device technologies (Si CMOS,	InP			
Title: FLASH - Scaling Fiber Arrays at Near Perfect Beam Qual	ity		-	13.000	16.31
Description: The goal of the FLASH program is to demonstrate that project 100-kW-class beams with near perfect beam quality variety of high-energy laser weapons applications. To accompli weight of high-power fiber lasers while increasing their robustne and (2) develop and demonstrate light-weight, high-power optic combination techniques for reducing necessary beam-projection compensation for atmospheric turbulence. The completed high of air, space, and ground targets at mission relevant ranges.	or and very high electrical-to-optical efficiency capable of enalish these ends, FLASH will (1) greatly reduce the overall size ess consistent with tactical and long-endurance aircraft integral phased arrays and ultra-high bandwidth target-in-the-loop or profiles consistent with deployment in aircraft and near-per	bling a e and ration, beam fect			

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B. Accomplishments/Planned Programs (\$ in Millions)		FY 201	3 FY 2014	FY 2015	
FY 2014 Plans: - Demonstrate an array of approximately 1.2 kW fiber-lasers confelectrical-to-optical efficiency. - Evaluate 21-element array system adaptive optical performance. - Demonstrate target-in-the-loop phase-locking on stationary and	ce under various atmospheric and sea-surface conditions.	>30%			
FY 2015 Plans: - Develop and test a coherently combinable, flight-worthy fiber la consistent with system integration on tactical aircraft. - Finish a comprehensive system design review of the entire last systems, and beam steering.		er			
Title: Direct SAMpling Digital ReceivER (DISARMER)			- 2.000	2.000	
Description: The goal of the Direct SAMpling Digital ReceivER (analog-to-digital converter (ADC) capable of directly sampling the receivers are limited in dynamic range by both the electronic mix optical clock, the DISARMER program will allow for mixer-less distate of the art. Such a wide bandwidth, high fidelity receiver will systems with the potential to drastically reduce the cost, size and	e entire X-band (8 -12 GHz). Conventional electronic widebter and the back-end digitizers. By employing an ultra-stable igitization and thereby improve the dynamic range 100x ove I have applications in electronic warfare and signals intellige	and e r the			
The DISARMER program will design, fabricate, and test a hybrid This involves the integration of electronic and photonic circuits, p delivering a field programmable gate array with the necessary fire research efforts funded in PE 0602716E, Project ELT-01.	packaging of a mode-locked laser with ultralow jitter, and				
FY 2014 Plans: - Define system architecture and flow-down metrics for individua - Design a quantizer chip that will incorporate a hold/reset switch and an encoder to convert the optical output of the photonic proc - Design remote sampling head to incorporate electronic RF from	h for each photodetector, an electronic quantizer capable of cessor to a digital code.	5 bits,			
FY 2015 Plans: - Fabricate and perform preliminary test of opto-electronic quant - Complete system engineering of field programmable gate array					

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Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES		ect (Number/Name) 15 I MIXED TECHNOLOGY EGRATION	
B. Accomplishments/Planned Programs (\$ in Millions)		FY 2013	FY 2014	FY 2015
 Demonstrate direct sampling of a 4 GHz-wide bandwidth sign. 	al at 7 effective bits of fidelity.			
Title: Direct On-Chip Digital Optical Synthesis (DODOS)			-	4.50
Description: The development of techniques for precise freque revolutionized modern warfare. Frequency control is the enablin and position-sensing and navigation technology, among many consynthesis has been limited to laboratory environments due to the based synthesizers. Recent developments on the DARPA Qual Laser Science and Engineering (PULSE) programs have demor microscale resonators. Combined with technology and fabricati Microprocessor (POEM) and Diverse & Accessible Heterogeneous chip-scale integrated optical frequency synthesizer. Ubiquitous a similar disruptive capability in optical technology as microwave coherent optical communications, coherent synthesized-apertur standoff gas/toxin detection, and intrusion detection, among oth The Direct On-chip Digital Optical Synthesis (DODOS) program synthesizer, in a compact, robust package, suitable for deployments.	ng technology for radar, satellite and terrestrial communication of the core DoD capabilities. To date, however, optical frequence large size, relative fragility, and high cost of optical combinum Assisted Sensing and Readout (QuASAR) and in Ultranstrated the possibility of generating self-referenced combs in on techniques developed in the Photonically Optimized Embous Integration (DAHI) programs, it is now possible to developed low-cost robust optical frequency synthesis is expected to defrequency synthesis did in the 1940s, enabling high-bandwith LiDAR, portable high-accuracy atomic clocks, high-resolutions. will create a microscale, high-accuracy optical frequency	fast n pedded op a reate vidth		
FY 2015 Plans: - Develop DODOS system architecture. - Optimize wavelength dispersion and low-threshold operation of the image of the	of micro-resonator based combs.	17.00	0 19.000	
Description: The Low Cost Thermal Imager - Manufacturing (Lowork and will develop a pocket-sized and smartphone-integrated that allows it to be provided to large numbers of warfighters. Avacameras will facilitate new techniques and applications that coulcameras will allow a soldier to have practical thermal imaging cain darkness. The small size, weight and power (SWaP) thermal a cell phone with network capability for tactical intelligence, survivalenthy will be required in low-cost thermal imagers man cost optics and low-power signal processing. By the end of the	d, manufacturable, and practical thermal imager at a price prailability of very low cost and small form-factor infrared (IR) ld provide the decisive edge needed in modern battlefields. apability for locating warm objects (e.g., enemy combatants) camera will be integrated with a handheld device such as reillance and reconnaissance. In order to achieve this goal, ufactured using wafer- scale integration, vacuum packaging	ng oint These , low-		

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B. Accomplishments/Planned Programs (\$ in Millions)		FY 2013	FY 2014	FY 2015		
processor and optics. The camera will have wireless connectivity to PEO Soldier Sensors and Lasers (SSL), PM Optics USMC, USSOC		Army				
 FY 2013 Accomplishments: Established interim small form-factor camera integration. Demonstrated and delivered interim 640x480, 17 micrometer (μm) Demonstrated 640x480 12 um pixel LCTI-M camera and imagery. Finalized design of low cost IR optics for LCTI-M. Demonstrated wafer-level optics with good uniformity across the v Demonstrated an integrated smart phone and first prototype therm Initiated fabrication of 640x480- 10 μm-pitch microbolometers. Completed design of camera electronics. 	vafer.					
 FY 2014 Plans: Complete low-cost wafer-scale optics for LCTI-M camera. Demonstrate small-form-factor camera integration employing 3-D Deliver interim prototypes for testing. Deliver final 640x480 LCTI-M cameras with test results and 1280x 	·					
Title: Maskless Direct-Write Nanolithography for Defense Application	ns	14.47	6 -			
Description: The Maskless Direct-Write Nanolithography for Defense Applications program developed a maskless, direct-write lithography tool that addresses both DoD needs for affordable, high performance, Integrated Circuits (ICs) in small lots and the commercial market's need for highly customized, application-specific ICs. In addition, this program has provided a cost effective manufacturing technology for low volume nanoelectromechanical system (NEMS) and nanophotonic devices within the DoD. Transition will be achieved by installing maskless lithography tools into the Trusted Foundry and in commercial foundries, which will enable affordable incorporation of state-of-the-art semiconductor devices in new military systems, and allow for the cost-effective upgrade of legacy military systems.		the ctive hich				
 FY 2013 Accomplishments: Designed and built a 4th generation electron-beam column capability. Designed and built a compact electrode stack lens demonstrating. Designed and built a permanent magnet lens demonstrating an aximicroampere (μA) at the wafer plane. Demonstrated gray-scale patterning capability on wafers using mubling of 40 nm at a wafer current of 1.06 μA. 	100 kilovolts standoff. kial field which gives 15 nm blur at a current of 2.5	and a				

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Exhibit R-2A, RDT&E Project Justification: PB 2015 Defense Advanced Research Projects Agency Date: March 2014						
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	Project (Number/Name) MT-15 I MIXED TECHNOLOGY INTEGRATION				
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2013	FY 2014	FY 2015	
- Designed and fabricated a third generation pattern generator (CMOS) electrical test at full speed and at all "corners."	device and passed Complementary metal-oxide-semiconduc	ctors				
Title: Excalibur			3.035	-	_	
Description: The Excalibur program developed high-power elepowered by a fiber laser amplifier. These fiber-laser arrays are fielded on a variety of platforms with minimal impact on the plat an adaptive-optic capability to minimize beam divergence in the view beam steering for target tracking. With each Excalibur arrato 3 kilowatts (kW) per amplifier), high power air-to-air and air-tinfeasible because of laser system size and weight. In addition which provided an alternate route to efficiently reaching missio of the optical phased array architecture. Excalibur arrays are adding additional elements to the array. Excalibur provided the platforms, including all aircraft flying at altitudes below 50,000 fair-defense systems (MANPADS) and more capable air-to-air rechnology will enable these platforms to fly at lower altitude are as reconnaissance despite low-lying cloud cover. Further capatidentification, tracking, designation, precision defeat with minima. The Excalibur program also developed efficient high-power las. The potential of these arrays to scale to tactical power levels (farrays were designed to work in tandem with the core laser con Project TT-06. In addition a conceptual design and CONOPS system were developed to enable a near-term capability for low transition via industry, and will be incorporated into the Endura	e sufficiently lightweight, compact, and electrically efficient to a sufficiently lightweight, compact, and electrically efficient to a sufficiently original mission capabilities. Each array element possible presence of atmospheric turbulence, together with wide-field ray element powered by high power fiber laser amplifiers (at a sto-ground engagements have been enabled that were previously, this program developed kilowatt-class arrays of diode laser in-relevant power levels, and they tested the ultimate scalabilition formal to aircraft surfaces and scalable in size and power levels technology foundation for defense of next generation airborned against proliferated, deployed, and next-generation man-power levels to the surface of t	be sesses d-of-up usly s ty by ne ortable ur n et sining. er 2702E, CM)				
FY 2013 Accomplishments: - Demonstrated 11.2 kW of combined optical output from 16 fil - Demonstrated beam combining (coherent or spectral) of twel - Demonstrated coherent combining of a 19-element 2-D optic adaptive optics. - Designed and built a mobile 21-element optical phased array	nty-one 1-kW fiber laser amplifiers. cal phased array with a combined power of 21 kW and tip/tilt					
Title: Advanced Wide FOV Architectures for Image Reconstruction	·		6.395	-	_	

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Exhibit R-2A, RDT&E Project Justification: PB 2015 Defense Advanced Research Projects Agency			Date: N	/larch 2014		
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	MT-15	Project (Number/Name) MT-15 I MIXED TECHNOLOGY INTEGRATION			
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2013	FY 2014	FY 2015	
Description: The Advanced Wide FOV Architectures for Image addressed the passive imaging needs for multi-band, wide fiel ground platforms. The AWARE program sought to solve the treatment architectures by focusing on four major tasks: high spread plane array architecture; broadband focal plane array are The AWARE program has advanced integration of technologies cameras, including the technologies demonstrated in the relative aggregated the following programs: Lambda Scale, Broadband technologies will enable next-generation focal plane arrays (Flabricate very high pixel-count cameras for persistent surveilland).	d-of-view (FOV) and high-resolution imaging for ground and rechnological barriers to wide FOV, high resolution and multi-bace-bandwidth product (SBP) camera architecture; small-pitchitecture; and multi-band focal plane array architecture. The sest that enable wide field of view and high resolution and multied AWARE program in PE 0602716E, Project ELT-01. AWAI d, Multi-Band and Wide Field of View. The integration of the PAs) and cameras. Such focal plane arrays can also be used.	oand n pixel -band RE				
FY 2013 Accomplishments: Optimized broadband detector array fabrication and assemble 18 μm-pixel-pitch detector arrays to readout integrated circuits Finalized camera integration and demonstrated broadband Fabricated and demonstrated 1280x720, 5 μm-pixel-pitch Locultered and in brownout conditions. Conducted initial field tests for MWIR rifle scope. Delivered a camera with a 2Kx2K sensor to be used for evaluation Completed the development of an algorithm for imaging throadsense in the complete statement of the complete statement	s. (0.5 to 5 μm) performance with 1024x1024, 18 μm-pixel-pitch ong-Wave IR (LWIR) and Mid-Wave IR (MWIR) FPAs for imag luations under brownout landing conditions.	FPA. ging in				

C. Other Program Funding Summary (\$ in Millions)

N/A

Remarks

D. Acquisition Strategy

N/A

E. Performance Metrics

Specific programmatic performance metrics are listed above in the program accomplishments and plans section.

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Accomplishments/Planned Programs Subtotals

55.494

74.744

79.860